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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(TYP.)	I _D (A)	Q _g (TYP.)				
100	3.2at V _{GS} = 10 V	185	81.3 nC				

TO-220 Pin Configuration

N-Channel MOSFET

FEATURES

- Super Trench III
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (1			
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	 	
Continuous Drain Current /T 150 °C)	T _C = 25 °C		185	
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C	I _D	128	
Pulsed Drain Current (t = 100 μs)	I _{DM}	702	_ A	
Avalanche Current L = 0.1 mH		I _{AS}	180	
Single Avalanche Energy ^a	L = U.1 MH	E _{AS}	970	mJ
Mayimum Dayyar Dissination 3	T _C = 25 °C	В	320	w
Maximum Power Dissipation ^a	T _C = 100 °C	$ P_D$	159	
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	33	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.47	C/VV			

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. A



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	-	4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μА
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
		V _{DS} =80 V, V _{GS} = 0 V, T _J = 175 °C	-	-	2	mA
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	3.2	3.8	mΩ
Forward Transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 65 A	-	92	-	S
Dynamic ^b					`	
Input Capacitance	C _{iss}		-	5860	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	663	-	
Reverse Transfer Capacitance	C _{rss}		-	40	-	
Total Gate Charge ^c	Qg		-	81.3	-	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	31.3	-	
Gate-Drain Charge ^c	Q _{gd}		-	31.2	-	
Gate Resistance	R _g	f = 1 MHz	-	0.88	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	20	-	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_{L} = 1.67 \Omega$	-	11.5	-	7
Turn-Off Delay Time c	t _{d(off)}	$I_D \cong 65 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	48	-	ns
Fall Time ^c	t _f		-	9	-	1
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 μs)	I _{SM}		-	-	702	Α
Forward Voltage ^a	V _{SD}	I _F = 65 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}		-	78	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 65 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	-	Α
Reverse Recovery Charge	Q _{rr}		-	150	-	nC

Notes

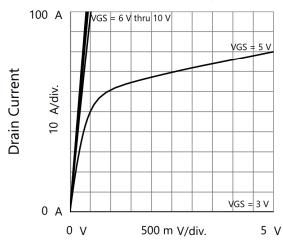
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

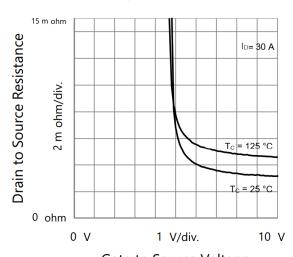




TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

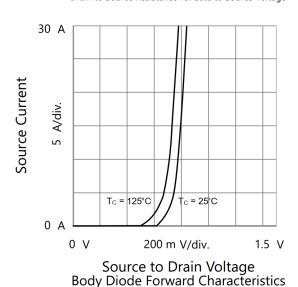


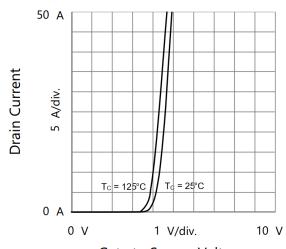
Drain to Source Voltage Output Characteristics



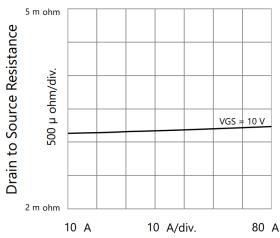
Gate to Source Voltage

Drain to Source Resistance vs. Gate to Source Voltage

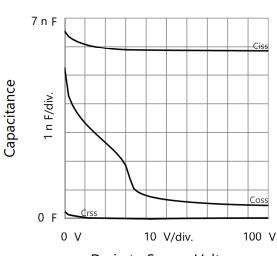




Gate to Source Voltage Transfer Characteristics



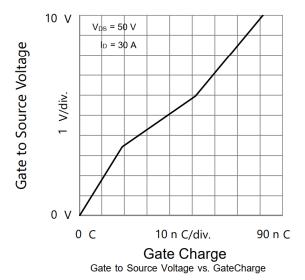
Drain Current
Drain to Source Resistance vs. Drain Current

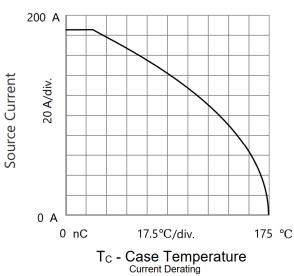


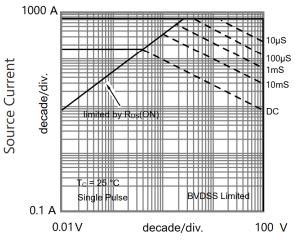
Drain to Source Voltage Capacitances

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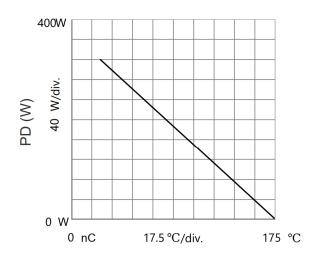
TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise noted)







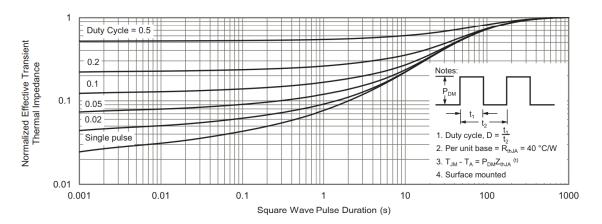




 T_{C} - Case Temperature $_{\mbox{\footnotesize Power Derating}}$



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

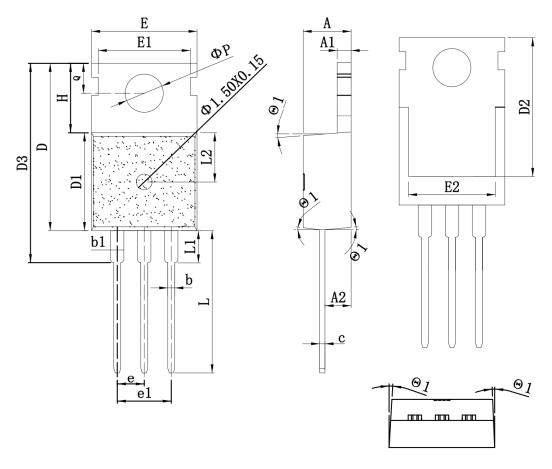
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



TO-220_3L-A PACKAGE OUTLINE

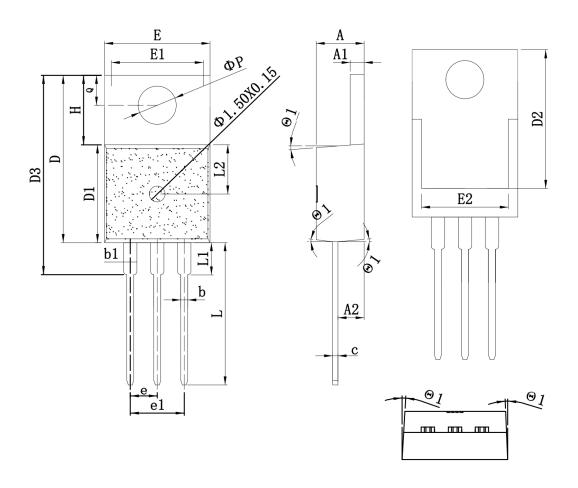


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
STWIBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
с	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm		SYMBOL	mm			
SYMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
С	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°





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